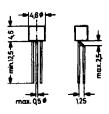
New Jersey Semi-Conductor Products, Inc.

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BF240, BF241

NPN Silicon Epitaxial Planar Transistors designed for emitter-grounded AM and FM amplifier stages





Plastic case \approx JEDEC TO-92 TO-18 compatible The case is impervious to light

Weight approximately 0.18 g Dimensions in mm

Absolute Maximum Ratings

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	40	v
Collector Emitter Voltage	V _{CEO}	40	v
Emitter Base Voltage	V _{EBO}	4	v
Collector Current	lc	25	mA
Base Current	l _B	2	mA
Power Dissipation at T _{amb} = 25 °C	P _{tot}	3001)	mW
Junction Temperature	Тј	150	°C
Storage Temperature Range	T _s	-55 +150	°C



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

BF240, BF241

Characteristics at $T_{amb} = 25 \text{ °C}$

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	Symbol	Min.	Тур.	Max.	Value
DC Current Gain at $V_{CE} \neq 10 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$ BF240 BF241	h _{FE} h _{FE}	67 36	- -	220 125	-
Base Emitter Voltage at $V_{CB} = 10$ V, $I_C = 1$ mA	VBE	650	700	740	mV
Collector Cutoff Current at $V_{CB} = 20 V$	Ісво	_	-	100	nA
Thermal Resistance Junction to Ambient	R _{thA}	_	-	420 ¹⁾	K/W
Collector Base Breakdown Voltage at $I_C = 10 \ \mu A$	V _{(BR)CBO}	40	-	-	V
Collector Emitter Breakdown Voltage at $I_c = 2 \text{ mA}$	V _{(BR)CEO}	40	-	-	v
Emitter Base Breakdown Voltage at $I_E = 10 \ \mu A$	V _{(BR)EBO}	4	-	_	v
Gain Bandwidth Product at $V_{CB} = 10$ V, $I_C = 1$ mA, $f = 100$ MHzBF240 BF241	fT f _T		430 400		MHz MHz
Feedback Capacitance at V_{CB} = 10 V, I _C = 1 mA, f = 1 MHz	-C _{re}	-	0.27	-	pF
Noise Figure (emitter grounded) at $V_{CB} = 10 \text{ V}$, $I_C = 1 \text{ mA}$ $g_s = 5 \text{ mS}$, $f = 200 \text{ kHz}$ $y_s = (6.6 - j 3.3) \text{ mS}$, $f = 100 \text{ MHz}$	F F		1.5 1.6	3.5 -	dB dB
Output Admittance at V _{CB} = 10 V, I _C = 1 mA, f = 10.7 MHz at V _{CB} = 10 V, I _C = 1 mA, f = 470 kHz	g _{oe} g _{oe}	-	-	10.5 8.3	μS μS